

Sneha Kabra

List of Publications by Year in descending order

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16
papers

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1478505

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16
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16
docs citations

16
times ranked

100
citing authors

#	ARTICLE	IF	CITATIONS
1	Modeling and Simulation of AlGaIn/GaN MOS-HEMT for Biosensor Applications. IEEE Sensors Journal, 2019, 19, 587-593.	4.7	45
2	An analysis for AlGaIn/GaN modulation doped field effect transistor using accurate velocity-field dependence for high power microwave frequency applications. Microelectronics Journal, 2006, 37, 1339-1346.	2.0	22
3	Performance Investigation of Novel Pt/Pd-SiO ₂ Junctionless FinFET as a High Sensitive Hydrogen Gas Sensor for Industrial Applications. IEEE Sensors Journal, 2021, 21, 13356-13363.	4.7	17
4	Performance Analysis and Optimization of Under-Gate Dielectric Modulated Junctionless FinFET Biosensor. IEEE Sensors Journal, 2021, 21, 18897-18904.	4.7	11
5	Comparative Analysis of Junctionless FinFET and Inverted Mode FinFET as Phosphine (PH ₃) Gas Sensor. , 2020, , .		10
6	Reliability Assessment of GaAs/Al _{0.3} In _{0.7} Junctionless FinFET in the Presence of Interfacial Layer Defects and Radiations. IEEE Transactions on Device and Materials Reliability, 2020, 20, 452-458.	2.0	10
7	Comparative Analysis of Dielectric Modulated Junctionless FinFET Biosensor and Junctionless DG MOSFET Biosensor for Medical Instrumentation. , 2019, , .		7
8	Analytical Modeling and Simulation of AlGaIn/GaN MOS-HEMT for High Sensitive pH Sensor. IEEE Sensors Journal, 2021, 21, 12998-13005.	4.7	7
9	Detection of Breast Cancer Cell-MDA-MB-231 by Measuring Conductivity of Schottky Source/Drain GaN FinFET. IEEE Sensors Journal, 2022, 22, 6108-6115.	4.7	4
10	Performance analysis of ScAlN/GaN High Electron Mobility Transistor (HEMT) for biosensing application. , 2020, , .		3
11	T-ZnO/AlGaIn/GaN HEMT Uric Acid Sensor-Sensitivity Analysis and Effect of Surface Wettability for Improved Performance. IEEE Sensors Journal, 2022, 22, 11819-11826.	4.7	3
12	Small-Signal Analysis of Double-Channel AlGaIn/GaN HEMT and MOSHEMT with Undoped Barrier for Microwave Applications. Journal of Electronic Materials, 2022, 51, 4095-4103.	2.2	3
13	Analysis of Interface Trap Charges of Double Gate Junctionless Nanowire Transistor (DG-JNT) for Digital Circuit Applications. , 2018, , .		1
14	Impact of laterally asymmetric channel and gate stack architecture on device performance of surrounding gate MOSFETs. Microwave and Optical Technology Letters, 2010, 52, 746-750.	1.4	0
15	Performance of AlGaIn/GaN based Common Drain Dual HEMT (CDD-HEMT) for high power applications. , 2019, , .		0
16	Stability and Reliability Performance of Double Gate Junctionless Transistor (DG-JLT) 6T SRAM. , 2021, , .		0